

Contents

<i>Acknowledgements</i>	xii
<i>Contents</i>	xiii
<i>List of Figures</i>	xvii
<i>List of Tables</i>	xxiii
<i>Abbreviations</i>	xxv
<i>PREFACE</i>	xxvii
Chapter 1: Introduction	1
1.1 Background of thin film transistor (TFT) research.....	2
1.2 Brief History and Principles of TFTs.....	4
1.2.1 Field-Effect Mobility (μ).....	8
1.2.2 ON/OFF ratio.....	9
1.2.3 Threshold Voltage (V_T).....	9
1.2.4 Subthreshold Swing (SS).....	10
1.3 TFT Components: Their Role in TFT Characteristics and Material Selection Procedure for Components.....	10
1.3.1 Gate Insulator (Dielectric).....	10
1.3.2 Semiconductor.....	13
1.3.3 Electrodes.....	15
1.4 Requirement of high- κ dielectric in TFT community: Their advantages and drawbacks.....	16
1.5 Role of Interfacial engineering in the improvement of TFT Device performance..	19
1.6 Ferroelectric Field Effect Transistor (FEFET) with ionic ferroelectric gate dielectric.....	22

1.6.1	Retention Time.....	23
1.6.2	Remnant Polarization.....	23
1.7	Scope and Objective of the Present Work.....	24
Chapter : 2 Experimental Part: Materials Synthesis & Characterization, Device Fabrication.....		29
2.1	Materials synthesis.....	30
2.1.1	Synthesis of Li-Al ₂ O ₃ ion-conducting gate-dielectric precursor solution....	31
2.1.2	Synthesis of TiO ₂ and Mn ₂ O ₃ precursor solution.....	31
2.1.3	Synthesis of SnO ₂ precursor solution.....	32
2.1.4	Synthesis of ferroelectric LiNbO ₃ precursor solution.....	32
2.1.5	Synthesis of a-C precursor solution.....	32
2.2.	Device fabrication.....	33
2.2.1	Substrate cleaning.....	33
2.2.2	Device fabrication with a single dielectric layer.....	35
2.2.2.1	SnO ₂ TFT with Li-Al ₂ O ₃ gate-dielectric.....	35
2.2.2.2	SnO ₂ TFT with LiNbO ₃ gate-dielectric.....	35
2.2.3	Device fabrication with bilayer dielectric stack.....	36
2.2.3.1	SnO ₂ TFT with bilayer TiO ₂ /Li-Al ₂ O ₃ dielectric.....	36
2.2.3.2	SnO ₂ TFT with bilayer Mn ₂ O ₃ /Li-Al ₂ O ₃ dielectric.....	37
2.2.3.3	SnO ₂ TFT with multilayer Li-Al ₂ O ₃ /LiNbO ₃ /Li-Al ₂ O ₃ dielectric.....	38
2.2.3.4	SnO ₂ TFT with bilayer Li-Al ₂ O ₃ /a-C dielectric.....	39
2.3	Material characterization and Electrical characterization.....	39
2.3.1	X-ray diffraction.....	39
2.2.2	UV-visible spectroscopy.....	40
2.3.3	Atomic force microscopy.....	40

2.3.4	X-ray photoelectron spectroscopy.....	41
2.3.5	Scanning electron microscopy.....	41
2.3.6	Current measurement.....	42
2.3.7	Capacitance vs. frequency measurement.....	42
2.3.8	Polarization vs. Electric field measurement.....	43
2.3.9	Thin-film transistor characterization.....	43
Chapter 3: Solution-processed Low Voltage Metal-Oxide Transistor by using TiO ₂ /Li-Al ₂ O ₃ stacked Gate Dielectric.....		45
3.1	Introduction.....	46
3.2	Results and discussions.....	48
3.2.1	Grazing Incidence X-ray Diffraction pattern of Thin Films.....	48
3.3.2	Surface Morphologies of Thin Films.....	49
3.2.3	Dielectric and Electrical characterization.....	50
3.2.4	Electrical Characterization of Single and Bilayer Thin Film Transistor.....	52
3.3	Conclusions.....	57
Chapter 4: Gate Interface Engineering for Sub-volt Metal-Oxide Transistor Fabrication by Using Ion-conducting Dielectric with Mn ₂ O ₃ Gate Interface.....		59
4.1	Introduction.....	60
4.2	Results and discussions.....	62
4.2.1	Powder XRD and GIXRD characterization of Mn ₂ O ₃	62
4.2.2	X-ray photoemission spectroscopy (XPS) of Mn ₂ O ₃	63
4.2.3	UV-Vis absorption studies of thin films.....	64
4.2.4	Surface morphologies of different thin films.....	66
4.2.5	Cross-sectional SEM of TFT device.....	68
4.2.6	Variation of capacitance with frequency and current density with applied field (or voltage) of different dielectric films.....	68

4.2.7	TFT device characterization.....	71
4.3	Conclusions.....	76
Chapter 5: Solution processed Li-Al ₂ O ₃ /LiNbO ₃ /Li-Al ₂ O ₃ Stacked Gate Dielectric for a Low Operating Voltage Ferroelectric Thin Film Transistor.....		79
5.1	Introduction.....	80
5.2	Results and discussions.....	82
5.2.1	XRD Analysis	82
5.2.2	UV-Vis Spectra Study.....	84
5.2.3	Surface Morphology.....	85
5.2.4	Dielectric Properties.....	86
5.2.5	Electronic characteristics of Transistors.....	90
5.2.6	Retention Time.....	95
5.3	Conclusions	99
Chapter 6: Application of Microwave Synthesized Ultra-smooth a-C Thin Film for the Reduction of Dielectric/Semiconductor Interface Trap States of an Oxide TFT.....		101
6.1	Introduction.....	102
6.2	Results and discussions.....	104
6.2.1	Surface Morphology and Chemical State Study.....	104
6.2.2	Dielectric and Electronic Characterization of MIM Devices.....	107
6.2.3	Electronic Measurements of TFTs.....	109
6.3	Conclusions.....	114
Chapter 7: Conclusions and Future perspectives.....		115
7.1	Conclusions.....	116
7.2	Future perspectives.....	119
<i>References</i>		121
<i>List of Publications</i>		147